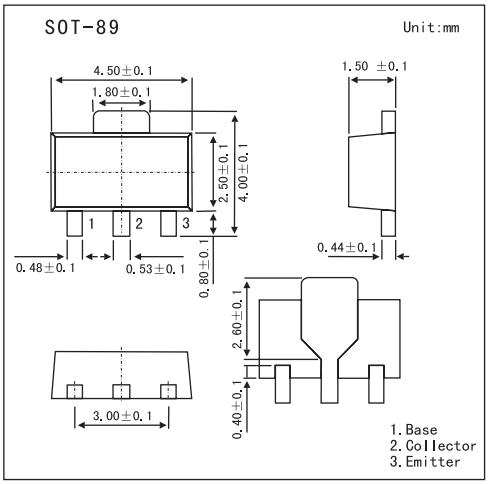
Small Signal Transistor

2SC5214



■ Features

- High fT fT=100MHz typ.
- Excellent linearity of dc forward current gain.
- High collector current ICM=1.5A.
- Small package for mounting.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Emitter-base voltage	V_{EBO}	4	V
Collector-emitter voltage	V_{CEO}	25	V
Peak collector current	I_{CM}	1.5	A
Collector current	I_C	1	A
Collector dissipation	P_C	500	mW
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Colllector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA,I_E=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0	4			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=100μA,R_{BE}=∞	25			V
Collector cutoff current	I_{CBO}	V_{CB}=25V,I_E=0			1	μA
Emitter cutoff current	I_{EBO}	V_{EB}=2V,I_C=0			1	μA
DC current gain	h_{FE}	V_{CE}=1V,I_C=500mA	55		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500mA,I_B=25mA			0.5	V
Gain bandwidth product	f_T	V_{CE}=6V,I_E=-10mA		100		MHz

■ hFE Classification

Marking	WC	WD	WE
hFE	55～110	90～180	150～300